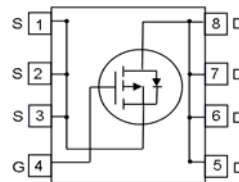
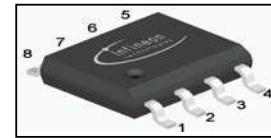


OptiMOS® P-Power-Transistor
Features

- single P-Channel in SO8
- Qualified according JEDEC for target applications
- 150°C operating temperature
- Super Logic Level (2.5V rated)
- Pb-free plating; RoHS compliant, Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}		-20	V
$R_{DS(on),max}$	$V_{GS}=4.5\text{ V}$	21	mΩ
	$V_{GS}=2.5\text{ V}$	34	
I_D		-8.9	A


PG-DSO-8


Type	Package	Marking	Lead free	Halogen free	Packing
BSO203SP H	PG-DSO-8	203SP	Yes	Yes	dry

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value		Unit
			10 secs	steady state	
Continuous drain current ¹⁾	I_D	$V_{GS} = -4.5\text{ V}$, $T_A = 25\text{ °C}$	-8.9	-7.0	A
		$V_{GS} = -4.5\text{ V}$, $T_A = 70\text{ °C}$	-7.1	-5.8	
		$V_{GS} = -2.5\text{ V}$, $T_A = 25\text{ °C}$	-7.0	-5.7	
		$V_{GS} = -2.5\text{ V}$, $T_A = 70\text{ °C}$	-5.6	-4.5	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_A = 25\text{ °C}$	-35.6		
Avalanche energy, single pulse	E_{AS}	$I_D = -8.9\text{ A}$, $R_{GS} = 25\text{ Ω}$	97		mJ
Gate source voltage	V_{GS}		±12		V
Power dissipation ¹⁾	P_{tot}	$T_A = 25\text{ °C}$	2.5	1.6	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150		°C
ESD class		JESD22-A114 HBM	1B (500V - 1 kV)		
Soldering temperature			260		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - soldering point	R_{thJS}		-	-	35	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint, $t_p \leq 10$ s	-	-	110	
		minimal footprint, steady state	-	-	150	
		6 cm ² cooling area ¹⁾ , $t_p \leq 10$ s	-	-	53	
		6 cm ² cooling area ¹⁾ , steady state	-	-	80	

Electrical characteristics, at $T_j=25$ °C, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0$ V, $I_D = -0.25$ mA	-20	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D = -100$ μ A	-0.6	-0.9	-1.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20$ V, $V_{GS} = 0$ V, $T_j = 25$ °C	-	-	-1	μ A
		$V_{DS} = -20$ V, $V_{GS} = 0$ V, $T_j = 150$ °C	-	-	-100	
Gate-source leakage current	I_{GSS}	$V_{GS} = -12$ V, $V_{DS} = 0$ V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 2.5$ V, $I_D = -7$ A	-	22	34	m Ω
		$V_{GS} = 4.5$ V, $I_D = -8.9$ A	-	15	21	
Gate resistance	R_G		-	3.3	-	Ω
Transconductance	g_{fs}	$ V_{DS} > 2 I_D R_{DS(on)max}$, $I_D = -7.1$ A	18	33	-	S

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μ m thick) copper area for drain connection. PCB is vertical in still air.

²⁾ See figure 3 for more detailed information

³⁾ See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V},$ $f=1\text{ MHz}$	-	2500	3750	pF
Output capacitance	C_{oss}		-	820	1230	
Reverse transfer capacitance	C_{rss}		-	680	1020	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-10\text{ V}, V_{GS}=-$ $4.5\text{ V}, I_D=-8.9\text{ A}, R_G=$ $6\ \Omega$	-	16	24	ns
Rise time	t_r		-	55	83	
Turn-off delay time	$t_{d(off)}$		-	45	68	
Fall time	t_f		-	74	111	

Gate Charge Characteristics⁴⁾

Gate to source charge	Q_{gs}	$V_{DD}=-10\text{ V}, I_D=-8.9\text{ A},$ $V_{GS}=0\text{ to }4.5\text{ V}$	-	-4	-6	nC
Gate charge at threshold	$Q_{g(th)}$		-	-4	-6	
Gate to drain charge	Q_{gd}		-	-11	-17	
Switching charge	Q_{sw}		-	-12	-18	
Gate charge total	Q_g		-	-26	-39	
Gate plateau voltage	$V_{plateau}$		-	-1.6	-	V
Output charge	Q_{oss}	$V_{DD}=-10\text{ V}, V_{GS}=0\text{ V}$	-	16	21	nC

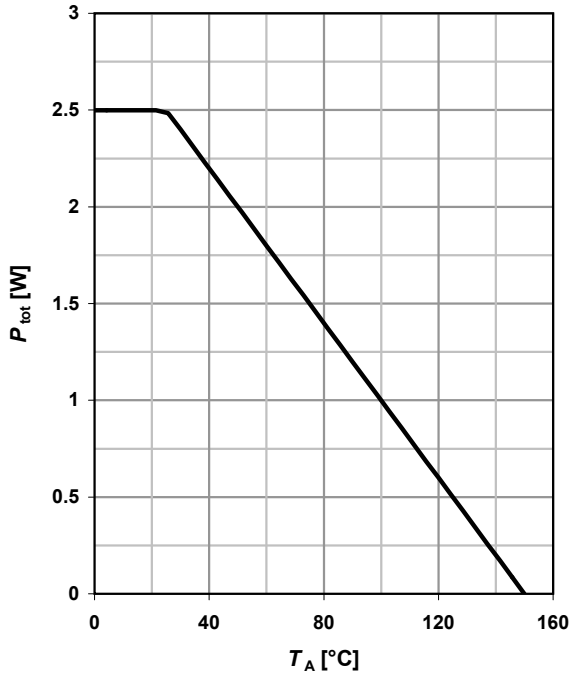
Reverse Diode

Diode continuous forward current	I_S	$T_A=25\text{ }^\circ\text{C}$	-	-	-3	A
Diode pulse current	$I_{S,pulse}$		-	-	-35.6	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=-8.9\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	-	1.1	V
Reverse recovery time	t_{rr}	$V_R=10\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	26	39	ns
Reverse recovery charge	Q_{rr}	$V_R=10\text{ V}, I_F=I_D,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	14	21	nC

⁴⁾ See figure 16 for gate charge parameter definition

1 Power dissipation

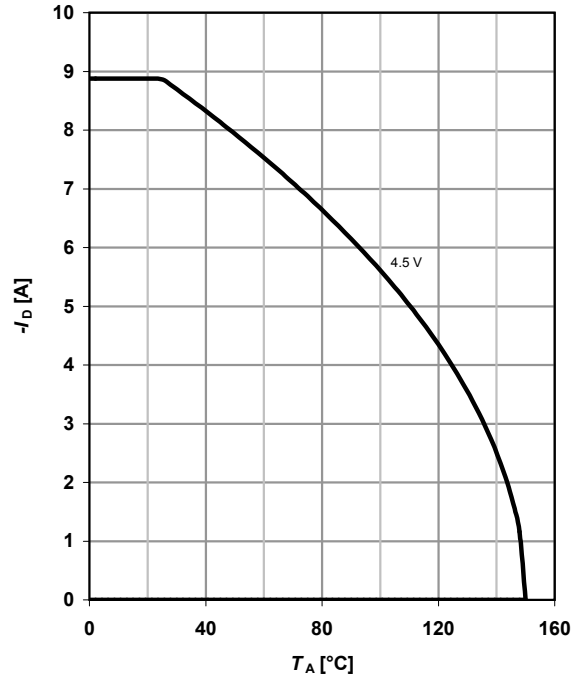
$P_{tot}=f(T_A); t_p \leq 10 \text{ s}$



2 Drain current

$I_D=f(T_A); t_p \leq 10 \text{ s}$

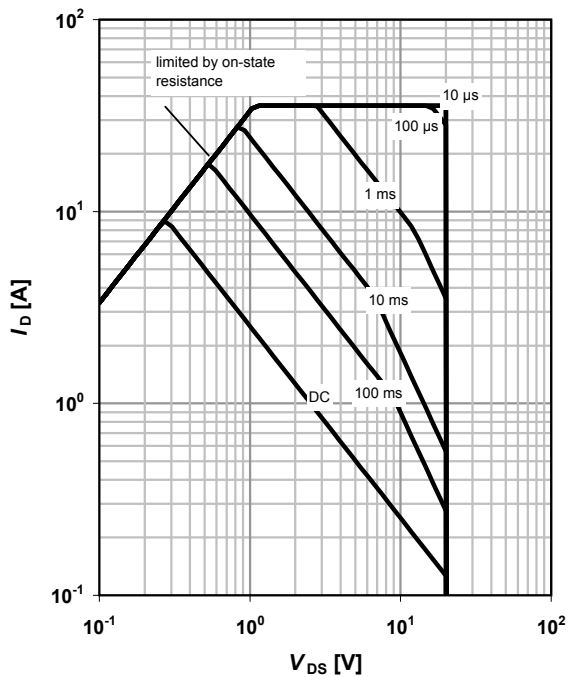
parameter: V_{GS}



3 Safe operating area

$I_D=f(V_{DS}); T_A=25 \text{ °C}^1; D=0$

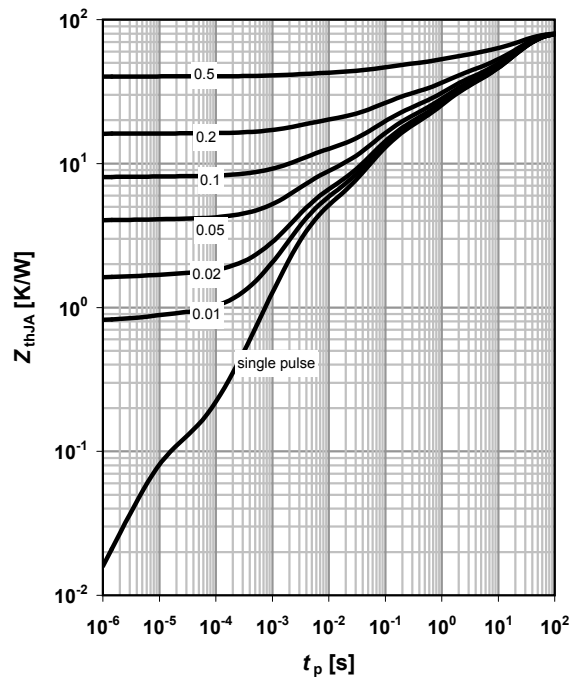
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJA}=f(t_p)^1$

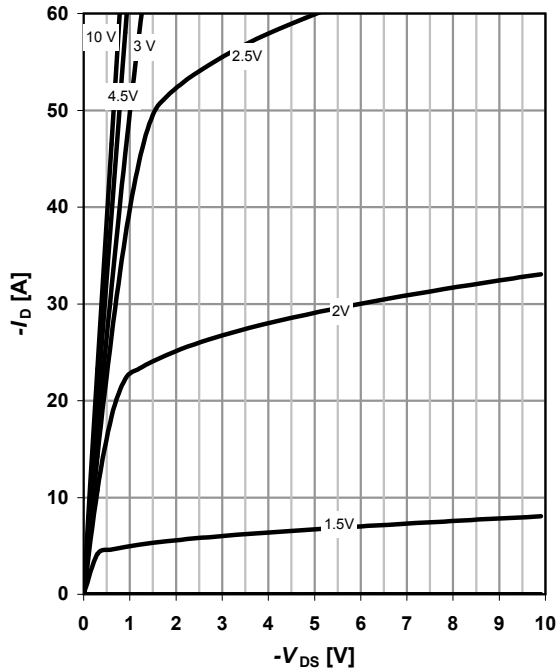
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

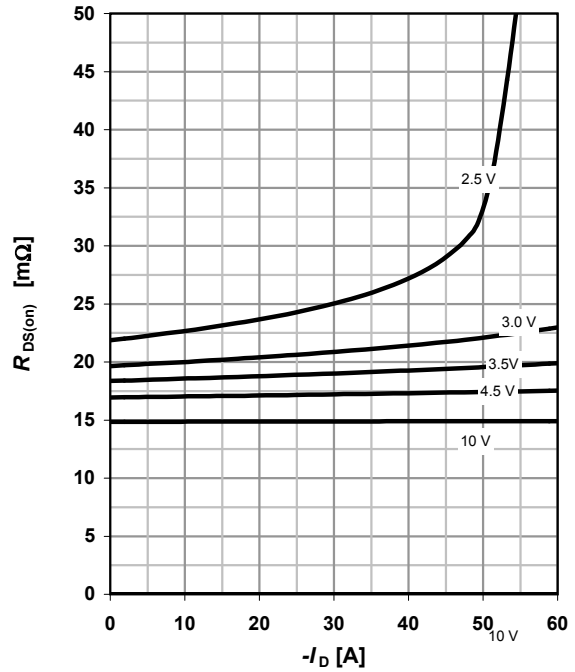
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

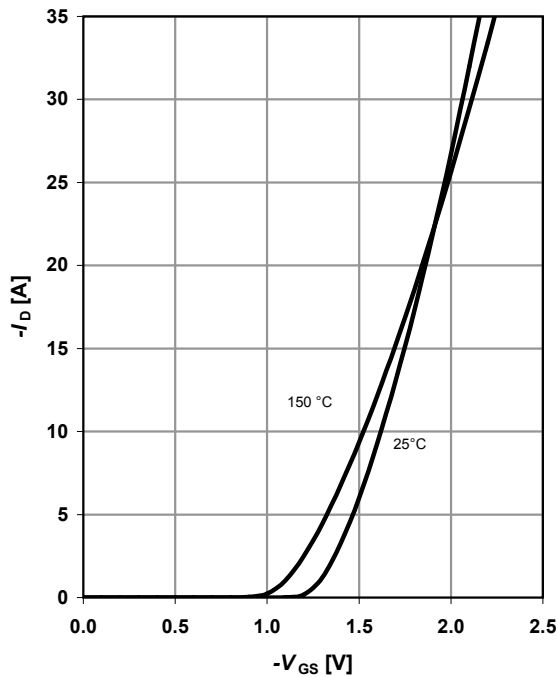
parameter: V_{GS}



7 Typ. transfer characteristics

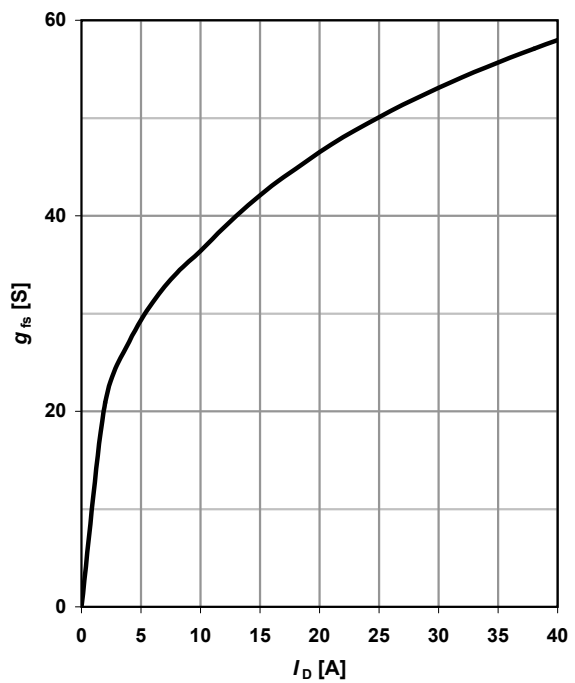
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



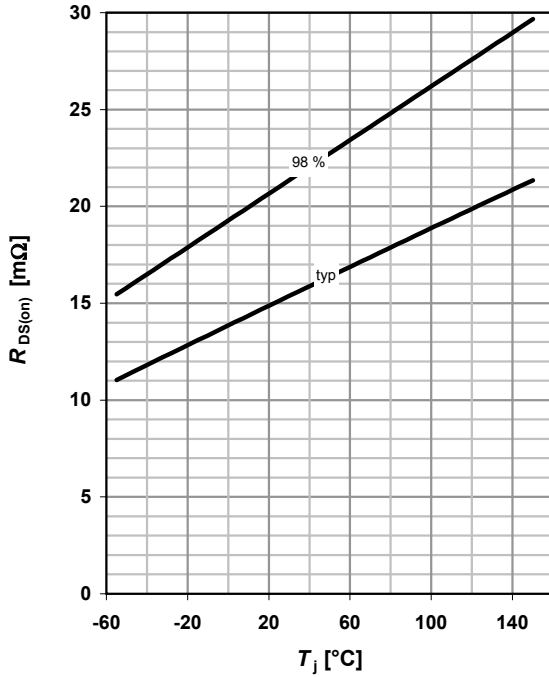
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



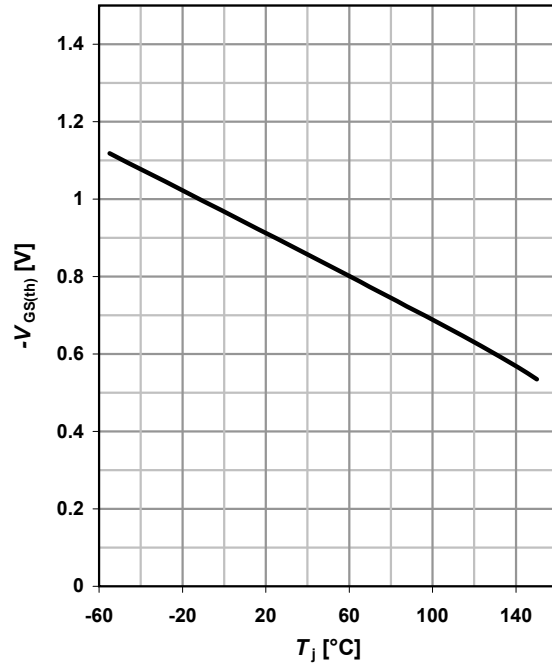
9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j); I_D = -8.9 \text{ A}; V_{GS} = -4.5 \text{ V}$



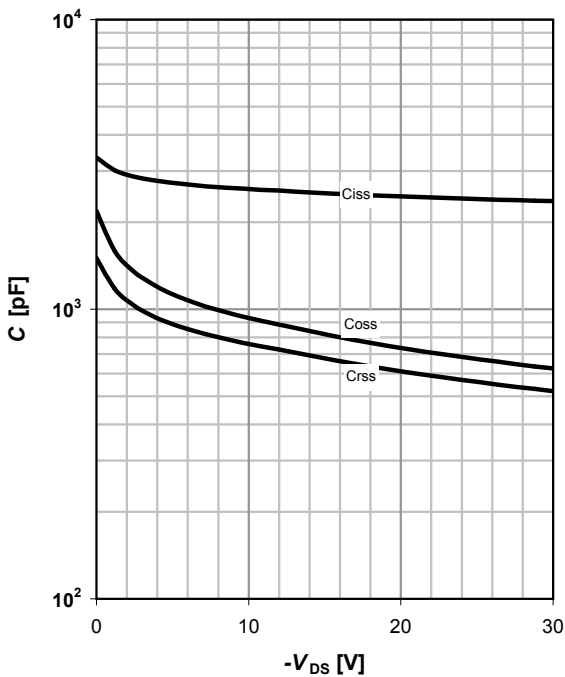
10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = -100 \mu\text{A}$



11 Typ. capacitances

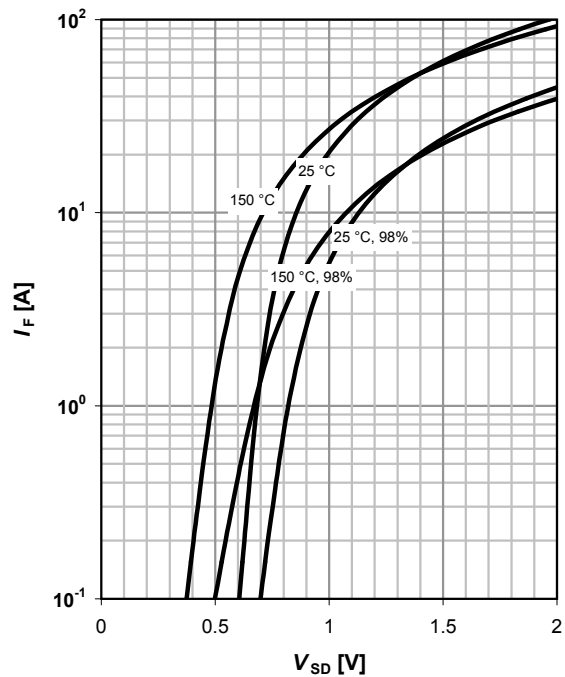
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



12 Forward characteristics of reverse diode

$I_F = f(V_{SD})$

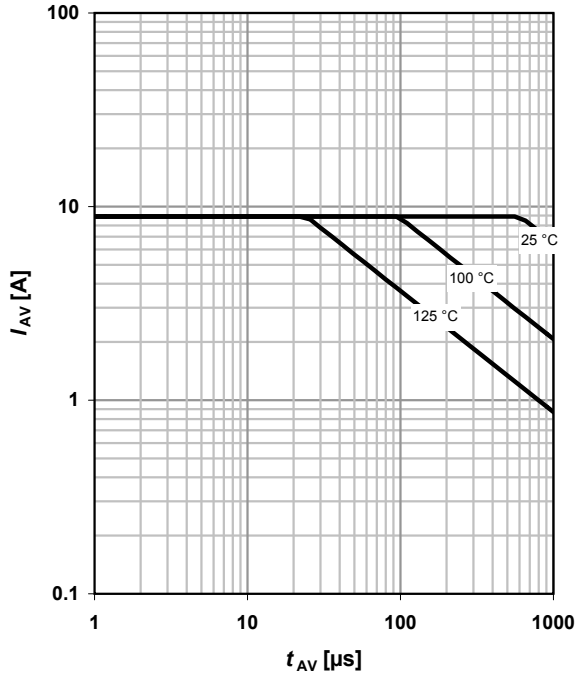
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

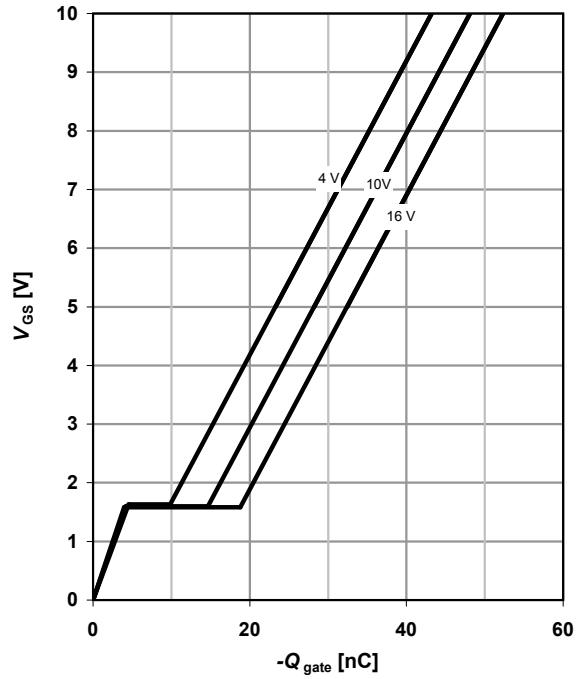
parameter: $T_{j(start)}$



14 Typ. gate charge

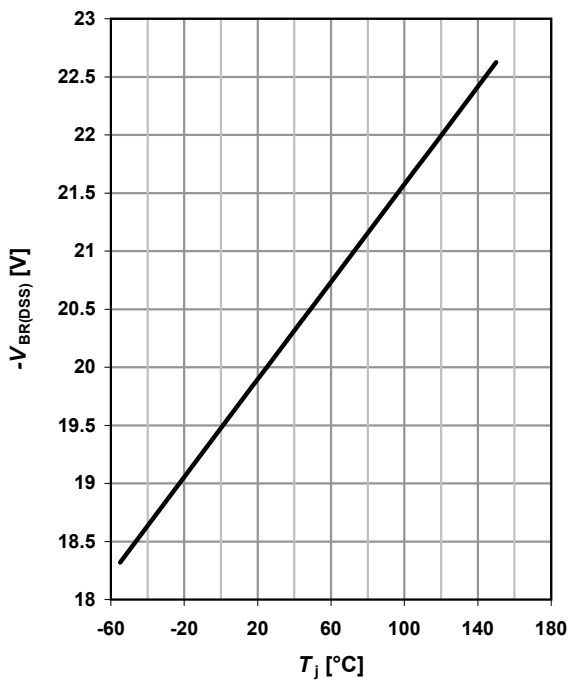
$V_{GS}=f(Q_{gate}); I_D=-8.9 \text{ A pulsed}$

parameter: V_{DD}

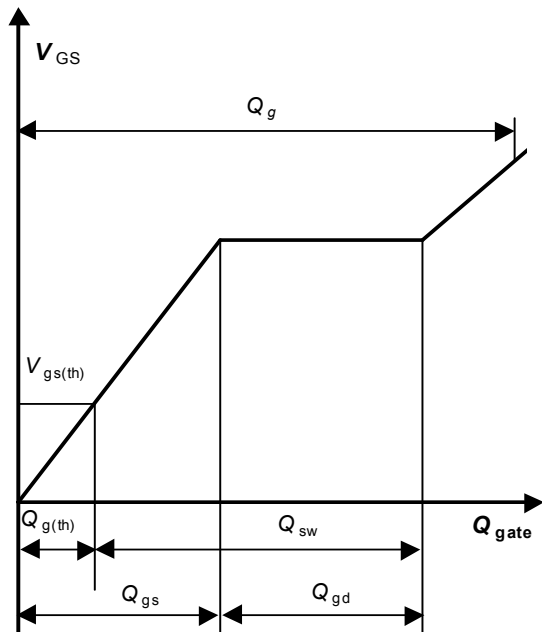


15 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

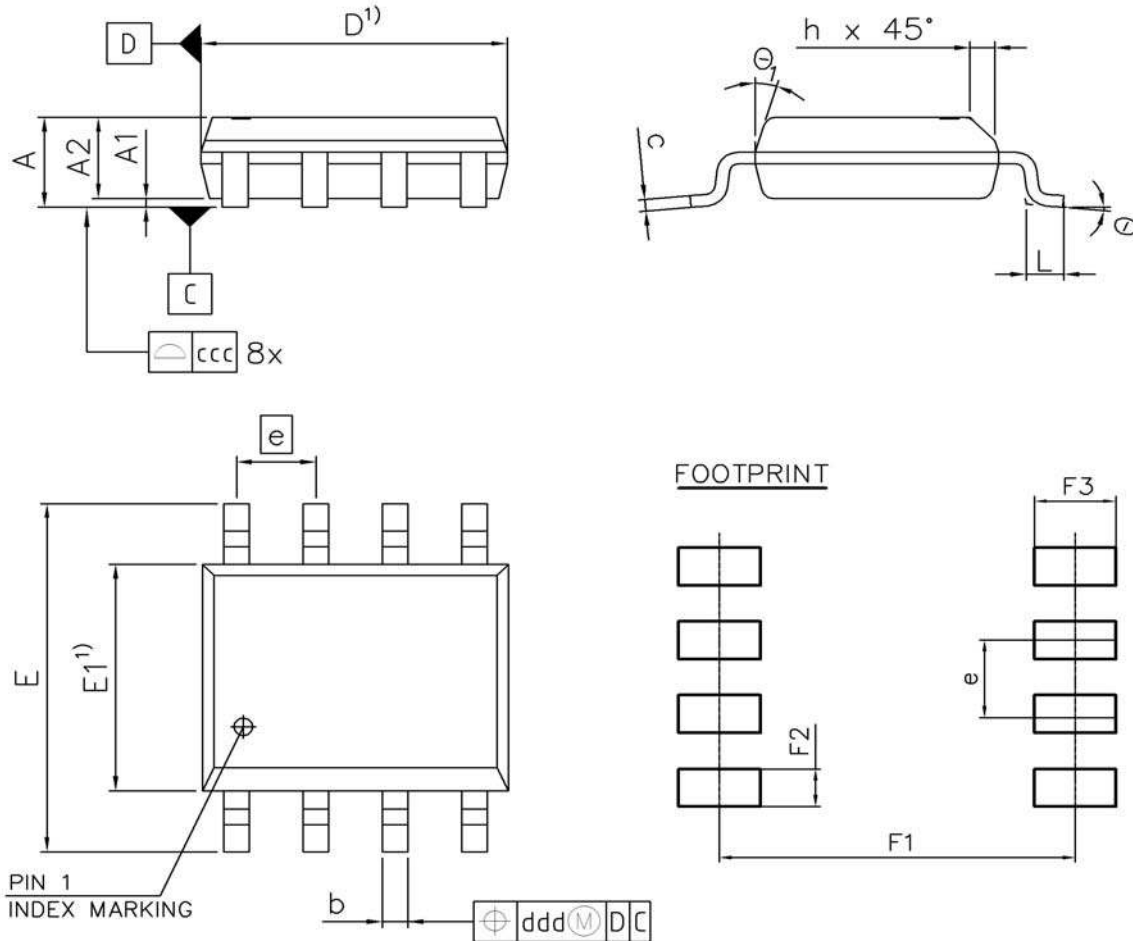


16 Gate charge waveforms



Package Outline

PG-DSO-8: Outline



1) DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.10	-	0.004	-
A2	1.25	1.65	0.049	0.065
b	0.35	0.51	0.014	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27		0.050	
N	8		8	
L	0.39	0.89	0.015	0.035
h	0.23	0.50	0.009	0.020
theta	0°	8°	0°	8°
theta1	-	19°	-	19°
ccc	0.10		0.004	
ddd	0.25		0.010	
F1	5.59	5.79	0.220	0.228
F2	0.55	0.75	0.022	0.030
F3	1.21	1.41	0.048	0.056

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